L Number	Hits	Search Text	DB	Time stamp
1	2	(BCB same (dielectric near (layer or film or matrix)) same (anneal$3)) and (dual near damascene)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 12:03
-	44	(dielectric near layer) with (nanotube or nanostructure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 12:01
-	0	(dielectric near matrix) with (nanotube or nanostructure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 15:55
-	1	(dielectric near matrix) same(nanotube or nanostructure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 15:55
-	1	(dielectric near matrix) same (nanotube or nanostructure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 15:56
-	832	dielectric near matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 15:57
-	1	(dielectric near matrix) and (ceramic near fibers)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 15:57
-	222	dielectric near (layer or film) with (fibers or whiskers)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 16:02
-	59	(dielectric near (layer or film) with (fibers or whiskers)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 16:47
-	288	((BCB) same dielectric) and (anneal$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 16:48
-	127	((BCB) with dielectric) and (anneal$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 16:48
-	5	((BCB) with dielectric) same (anneal$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 16:50
-	51	((BCB) with dielectric) same (damascene)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/18 16:50
-	8	((BCB) with dielectric) same (damascene) and anneal$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/22 16:43

-		6	((BCB) with dielectric) same (dual near damascene) and anneal$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/22 16:55